TOSHIBA CMOS DIGITAL INTEGRATED CIRCUIT SILICON MONOLITHIC

TC7WT125FU

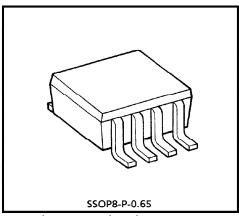
DUAL BUS BUFFER

The TC7WT125FU is a high speed CMOS DUAL BUS BUFFERS fabricated with silicon gate CMOS technology. It achieves the high speed operation similar to equivalent Bipolar Schottky TTL while maintaining the CMOS low power dissipation.

The input threshold levels are compatible with TTL output voltage.

The require 3-state control input \overline{G} to be set high to place the output into the high impedance.

All inputs are equipped with protection circuits against static discharge or transient excess voltage.

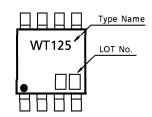


Weight: 0.02g (Typ.)

FEATURES

- High Speed $\cdots t_{pd} = 13ns (Typ.)$ at $V_{CC} = 5V$
- Low Power Dissipation $\cdots I_{CC} = 2\mu A$ (Max.) at Ta = 25°C
- Compatible with TTL outputs ··· V_{IL} = 0.8V (Max.), V_{IH} = 2.0V (Min.)
- Output Drive Capability 15 LSTTL Loads
- Symmetrical Output Impedance… |IOH| = IOL = 6mA (Min.)

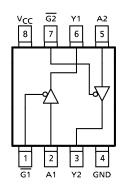
MARKING



MAXIMUM RATINGS (Ta = 25°C)

CHARACTERISTIC	SYMBOL	RATING	UNIT
Supply Voltage Range	Vcc	- 0.5~7	V
DC Input Voltage	VIN	-0.5~V _{CC} +0.5	V
DC Output Voltage	VOUT	-0.5~V _{CC} +0.5	V
Input Diode Current	Ικ	± 20	mA
Output Diode Current	lok	± 20	mA
DC Output Current	lout	± 35	mΑ
DC V _{CC} /Ground Current	lcc	± 37.5	mA
Power Dissipation	PD	300	mW
Storage Temperature	T _{stg}	-65∼150	°C
Lead Temperature (10 s)	TL	260	°C

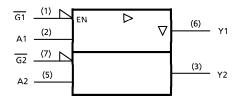
PIN ASSIGNMENT (TOP VIEW)



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LOGIC DIAGRAM



TRUTH TABLE

INP	UTS	OUTPUTS
G	Α	Υ
Н	×	Z
L	L	L
L	Н	Н

x : Don't Care Z : High Impedance

RECOMMENDED OPERATING CONDITIONS

CHARACTERISTIC	SYMBOL	RATING	UNIT
Supply Voltage	V _C C	4.5~5.5	V
Input Voltage	V _{IN}	0~V _{CC}	V
Output Voltage	Vout	0~V _{CC}	V
Operating Temperature	T _{opr}	- 40∼85	°C
Input Rise and Fall Time	t _r , t _f	0~500	ns

DC ELECTRICAL CHARACTERISTICS

CHARACTERISTIC	SYMBOL	DL TEST CONDITION		Vcc	Ta = 25°C			Ta = -40~85°C		UNIT
CHARACTERISTIC STIVIBUL TEST CONDITION		UNDITION	Vсс (V)	MIN.	TYP.	MAX.	MIN.	MAX.	UNIT	
High-Level	VIH			4.5~	2.0			2.0		V
Input Voltage	VIH			5.5	2.0		_	2.0	-	'
Low-Level	VIL			4.5~			0.8	_	0.8	V
Input Voltage	VIL			5.5						'
High-Level	\/a	$V_{IN} = V_{IH}$	$I_{OH} = -20\mu A$	4.5	4.4	4.5	_	4.4	_	V
Output Voltage	Voн	or V _{IL}	$I_{OH} = -6mA$	4.5	4.18	4.31	_	4.13	_	
Low-Level		V V	I _{OL} = 20μΑ	4.5	_	0.0	0.10	_	0.10	V
Output Voltage	VOL	$V_{IN} = V_{IL}$	I _{OL} = 6mA	4.5	_	0.17	0.26	_	0.33	
3-State Output	1	V _{IN} = = V _{IH} or V _{IL} V _{OUT} = V _{CC} or GND		5.5			± 0.5		± 5.0	
Off-State Current	loz			5.5		_	1 0.5	_	1 5.0	μΑ
Input Leakage	lisi	V _{IN} = V _{CC} or GND		5.5			± 0.1		± 1.0	Λ
Current	IN			3.5	_	_	_ 0.1	_	_ 1.0	μ A
	Icc	V _{IN} = V _{CC} or GND		5.5	_	_	2.0	_	20.0	μ A
Quiescent Supply		PER INPUT	: V _{IN} = 0.5V							
Current	^I CCT		or 2.4V	5.5	—	 	2.0	—	2.9	mΑ
		OTHER INPUT: V_{CC} or GND								

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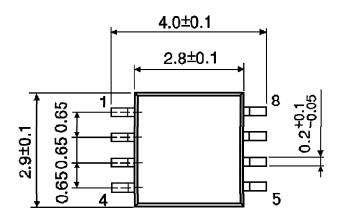
AC ELECTRICAL CHARACTERISTICS (Input $t_r = t_f = 6ns$)

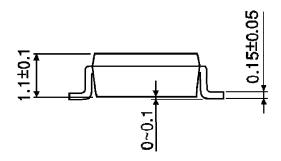
CHARACTERISTIC	CVMBOL	TEST CO	TEST CONDITION		Ta = 25°C			Ta = -40~85°C		UNIT
CHARACTERISTIC	SYMBOL		CL	Vcc	MIN.	TYP.	MAX.	MIN.	MAX.	UNIT
Output Transition	^t TLH	_	FO	4.5	_	7	12	-	15	nc
Time	tTHL		50	5.5	_	6	11	_	14	ns
		_		4.5	_	15	25	_	31	ns
Propagation Delay	t _{pLH}		50	5.5	_	13	22	_	28	
Time	tpHL		150	4.5	_	21	33	_	41	
				5.5	_	18	29	_	37	
	^t pZL ^t pZH	$R_L = 1k\Omega$	50	4.5	_	17	30	_	38	ns
Output Enable Time				5.5	_	14	27	_	34	
			150	4.5	_	23	38	_	48	
				5.5	_	20	34	_	43	
Output Disable Time	^t pLZ ^t pHZ	$R_L = 1k\Omega$	50	4.5	_	16	30	_	38	
				5.5	_	13	27	_	34	ns
Input Capacitance	CIN	_	_	_	_	5	10	_	10	рF
Output Capacitance	COUT	_	_	_	_	10	_		_	рF
Power Dissipation Capacitance	C _{PD}	(Note 1)	_	_	_	32	_	_	_	pF

(Note 1): CpD is defined as the value of the internal equivalent capacitance which is calculated from the operating current consumption without load. Average operating current can be obtained by the equation: $|CC(opr)| = CpD \cdot VCC \cdot f|N + |CC|/2$ (per Gate)

OUTLINE DRAWING SSOP8-P-0.65

Unit: mm





Weight: 0.02g (Typ.)